0 09/ldo4, 5do

L Number	Hits	Search Text	DB	Time stamp
1	23255	pixel near6 electrode	USPAT;	2003/12/15 09:10
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	98106	capacit\$8 near6 electrode	USPAT;	2003/12/15 09:10
			US-PGPUB;	
			EPO; JPO;	
i			DERWENT:	
			IBM_TDB	
3	403004	insulator or (insulating near6 layer)	USPAT:	2003/12/15 09:12
		i meanant et (meananng neane rayer)	US-PGPUB;	2000, 12, 10 00. 12
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
4	77283	capacit\$8 near6 line	USPAT;	2003/12/15 09:12
'	17200	Supulification into	US-PGPUB;	2000/12/10 03.12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	28697	gate near6 insulating near6 layer	USPAT:	2003/12/15 09:13
	20091	gate nearo insulating nearo layer	US-PGPUB:	2003/12/13 09.13
			EPO; JPO;	
1				
			DERWENT;	
6	126217	mata naoré alastrada	IBM_TDB	2002/42/45 00:44
6	136317	gate near6 electrode	USPAT;	2003/12/15 09:14
			US-PGPUB;	
			EPO; JPO;	
·			DERWENT;	
<b>,</b>	4004	/ which a 200 shorted day and / 200 shorted day 1 2	IBM_TDB	00004045 00:45
7	1264	(pixel near6 electrode) and (capacit\$8 near6 electrode) and	USPAT;	2003/12/15 09:15
		(insulator or (insulating near6 layer)) and (capacit\$8 near6	US-PGPUB;	:
ĺ	!	line) and (gate near6 insulating near6 layer) and (gate near6	EPO; JPO;	
]		electrode)	DERWENT;	
			IBM_TDB	00004045
8	15	(pixel near6 electrode) near6 (capacit\$8 near6 electrode)	USPAT;	2003/12/15 09:15
l		near6 (insulator or (insulating near6 layer)) near6 (capacit\$8	US-PGPUB;	
		near6 line) near6 (gate near6 insulating near6 layer) near6	EPO; JPO;	
		(gate near6 electrode)	DERWENT;	
			IBM_TDB	